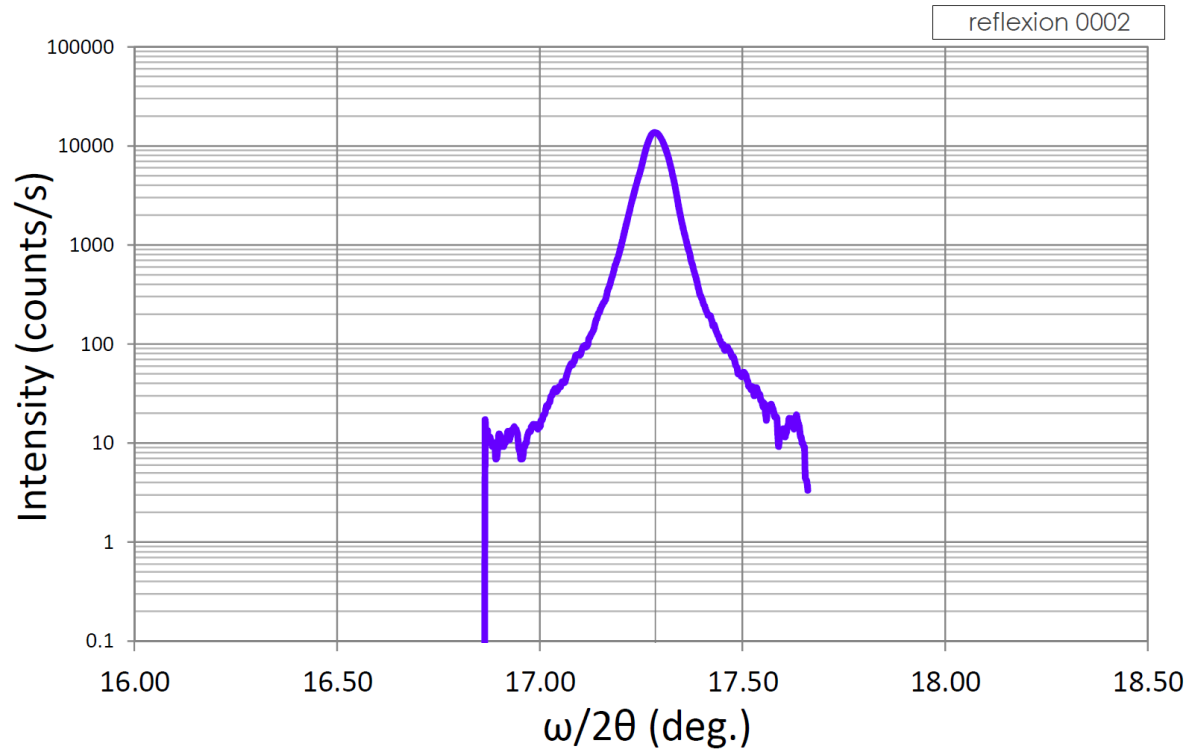


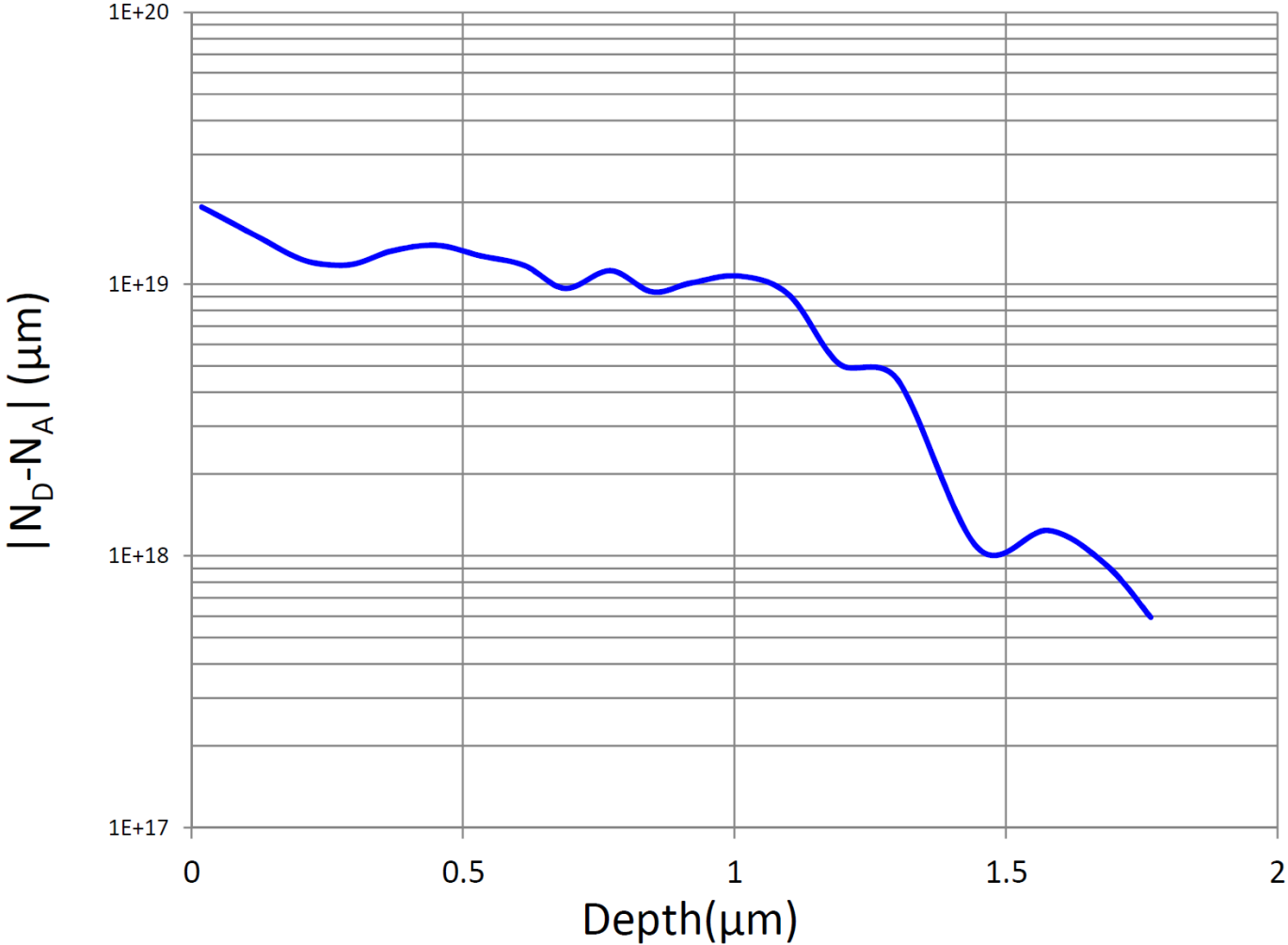
X-Ray Diffraction



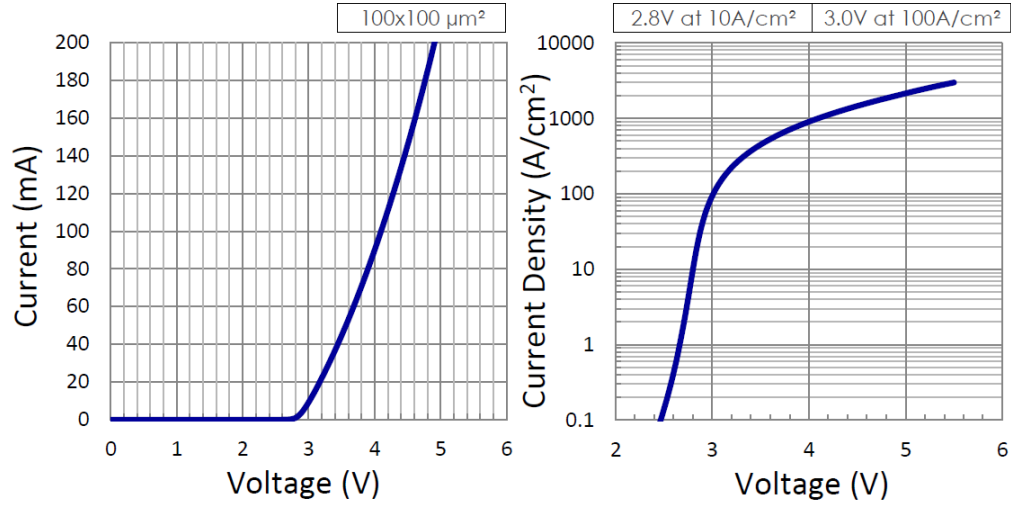
Peak	InGaN QW	GaN	AlGaN barrier	AlGaN
Diffraction Angle		17.285 °		
Intensity		1375,0		
FWHM		252 "		

InGaN QW	
In content	-
QW thickness	-
barrier thickness	-

C-V Measurements



I-V Characteristics



P-GaN Electrical Properties (TLM)

